

# EE 232: Lightwave Devices

## Lecture #12 – Spontaneous emission

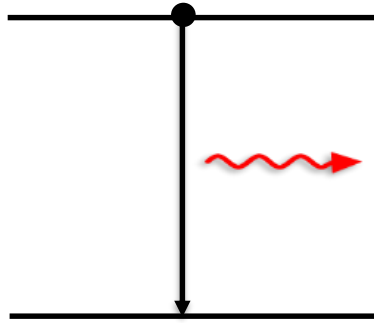
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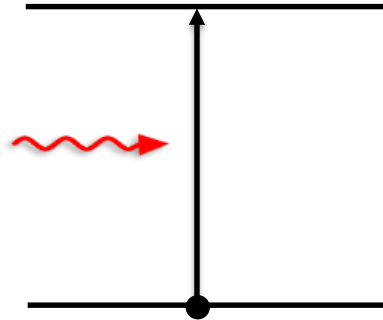
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# Two-level system

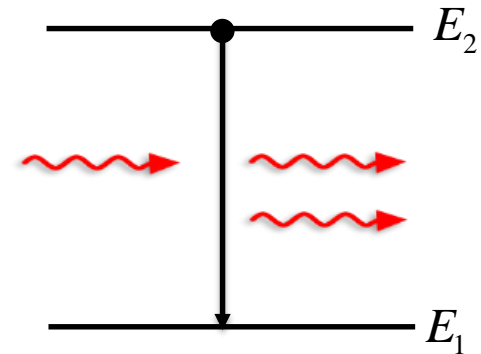
Spontaneous emission



Absorption



Stimulated emission



$A_{21}$  = Spontaneous emission rate

$B_{21}\rho(\hbar\omega)$  = Stimulated emission rate

$B_{12}\rho(\hbar\omega)$  = Absorption rate

$\rho(\hbar\omega)$  = Spectral photon density

$$\frac{dN_2}{dt} = -A_{21}N_2 - B_{21}\rho(\hbar\omega)N_2 + B_{12}\rho(\hbar\omega)N_1$$

$$\frac{dN_2}{dt} = 0 \quad (\text{steady state})$$

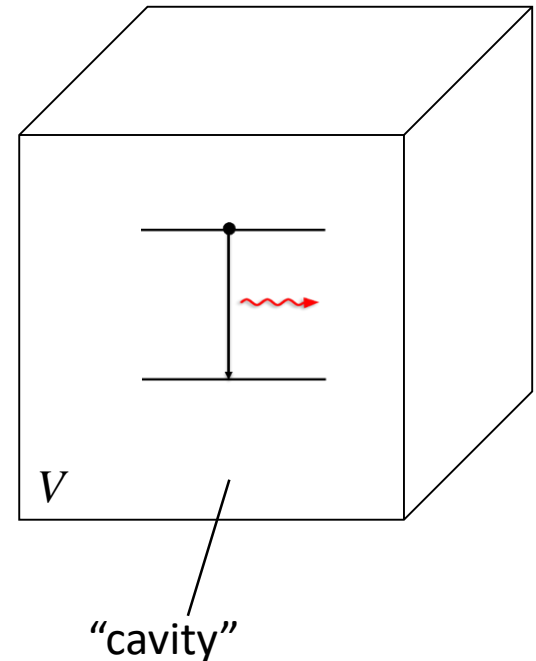
$$\rightarrow \rho(\hbar\omega) = \frac{A_{21} / B_{21}}{(N_1 / N_2)(B_{12} / B_{21}) - 1}$$

# Photon mode density

We place our two-level system in a “cavity”

What are the density of photon modes in this cavity?

$$\begin{aligned}\text{Mode density} &= \frac{1}{V} \sum_k \\ &= \frac{1}{V} \int \frac{2d^3\mathbf{k}}{(2\pi)^3 / V} \quad (\text{factor of 2 accounts for polarization}) \\ &= \int \frac{8\pi k^2 dk}{(2\pi)^3} \\ &= \int \frac{k^2 dk}{\pi^2} \quad \omega = \frac{c}{n} k \quad \frac{d\omega}{dk} = \frac{c}{n} \\ &= \int \frac{\omega^2 / (c/n)^2}{\pi^2 \hbar} \frac{d(\hbar\omega)}{c/n} \\ &= \int \frac{\omega^2 n^3}{\pi^2 \hbar c^3} d(\hbar\omega) \\ &= \int \rho_{mode} d(\hbar\omega)\end{aligned}$$



$$\rho_{mode} = \frac{\omega^2 n^3}{\pi^2 \hbar c^3} \quad (\text{modes/cm}^3/\text{eV})$$

# Relations between the coefficients

$$n_{ph}(\hbar\omega) = \frac{1}{\exp\left(\frac{\hbar\omega}{kT}\right) - 1} \quad \text{Bose-Einstein distribution (photons per state)}$$

$$\rho(\hbar\omega) = \rho_{mode}(\hbar\omega)n_{ph}(\hbar\omega)$$

$$\rho(\hbar\omega) = \frac{\omega^2 n^3}{\pi^2 \hbar c^3} \frac{1}{\exp\left(\frac{\hbar\omega}{kT}\right) - 1}$$

Recall, we also derived

$$\rho(\hbar\omega) = \frac{A_{21}/B_{21}}{(N_1/N_2)(B_{12}/B_{21}) - 1}$$

These equations must be equal to each other. This is only possible if:

$$\begin{aligned} N_1/N_2 &= \exp\left(\frac{\hbar\omega}{kT}\right) \\ B_{12} &= B_{21} \\ A_{21}/B_{21} &= \rho_{mode}(\hbar\omega) \end{aligned}$$

# Spontaneous emission

Transition rate from  
State 2 to State 1

$$\begin{aligned}R_{2 \rightarrow 1} &= A_{21}N_2 + B_{21}\rho(\hbar\omega)N_2 \\ &= B_{21}\rho_{mode}(\hbar\omega)N_2 + B_{21}\rho_{mode}(\hbar\omega)n_{ph}(\hbar\omega)N_2 \\ &= N_2B_{21}\rho_{mode}(\hbar\omega)\left[1 + n_{ph}(\hbar\omega)\right]\end{aligned}$$

↑  
stimulated  
emission  
from **one**  
photon in  
each mode

↙  
stimulated  
emission  
from ***n<sub>ph</sub>***  
photons in  
each mode

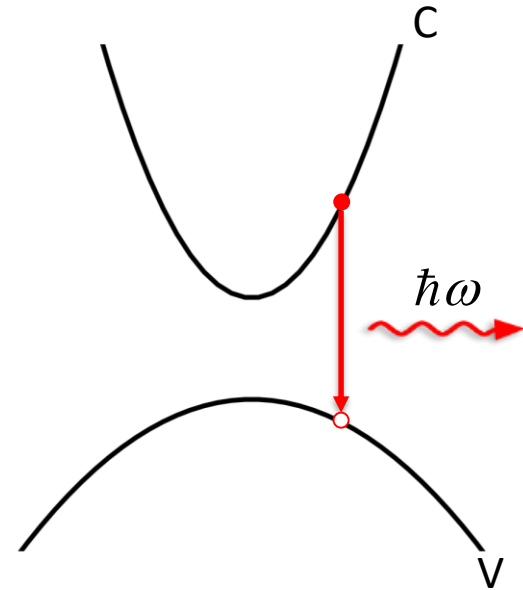
Spontaneous emission can be interpreted as the stimulated emission from a single photon in each optical mode.

# Spontaneous emission in semiconductor

$$r_{\text{spon}} = \frac{2}{V} \sum_{k_c} \sum_{k_v} \frac{2\pi}{\hbar} |H_{cv}|^2 \delta(E_e - E_h - \hbar\omega) f_c (1 - f_v)$$

$$|H_{cv}|^2 = \left| \langle \psi_c | -\frac{qA_0}{2m_0} \hat{e} \cdot \mathbf{p} | \psi_v \rangle \right|^2$$

We need to relate the magnitude of the vector potential to the mode density.



$$\text{EM energy density} = \frac{\rho_{\text{mode}}(\hbar\omega)(1)V\hbar\omega}{V}$$

$$= \rho_{\text{mode}}(\hbar\omega)\hbar\omega$$

$$\text{EM energy density} = \frac{1}{2} \epsilon_0 n^2 E_0^2$$

$$= \frac{1}{2} \epsilon_0 n^2 \omega^2 A_0^2$$

$$A_0^2 = \frac{2\rho_{\text{mode}}(\hbar\omega)\hbar\omega}{\epsilon_0 n^2 \omega^2 \hbar}$$

$$= \frac{2n\omega}{\epsilon \pi^2 c^3}$$

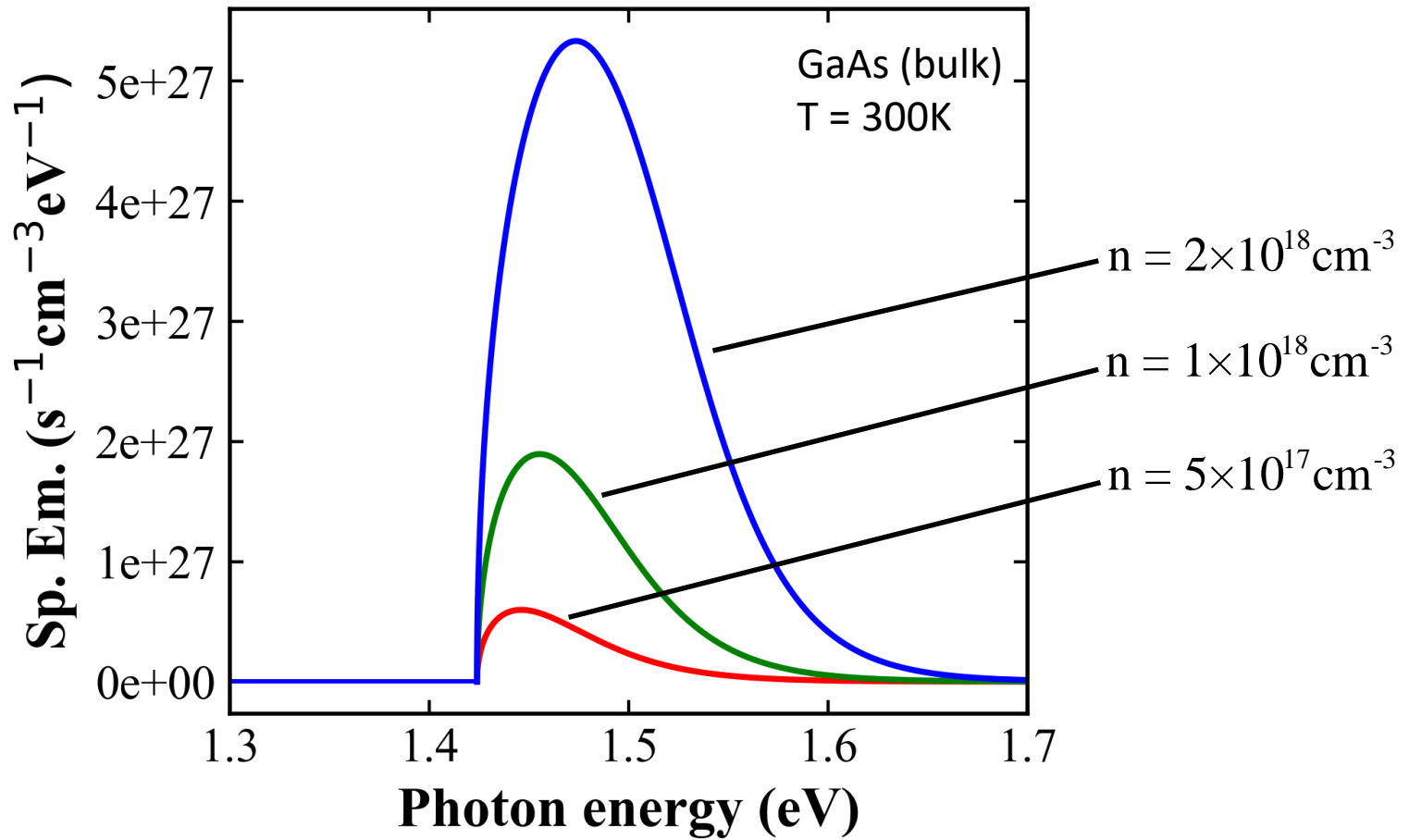
# Spontaneous emission in semiconductor

$$\begin{aligned}
 r_{\text{spont}}(\hbar\omega) &= \frac{2}{V} \sum_{k_c} \sum_{k_v} \frac{2\pi}{\hbar} |H_{cv}|^2 \delta(E_e - E_h - \hbar\omega) f_c (1 - f_v) \\
 &= \frac{2\pi}{\hbar} \frac{2}{V} \frac{q^2}{(2m_0)^2} \frac{2n\hbar\omega}{\epsilon_0 \pi^2 c^3} \sum_{k_c} \sum_{k_v} |H_{cv}|^2 \delta(E_e - E_h - \hbar\omega) f_c (1 - f_v) \\
 &= C_0 \left( \frac{n^2 \omega^2}{\pi^2 \hbar c^2} \right) \sum_{k_c} \sum_{k_v} |\hat{e} \cdot \mathbf{p}_{cv}|^2 \delta(E_e - E_h - \hbar\omega) f_c (1 - f_v)
 \end{aligned}$$

Spontaneous emission spectrum  $\text{cm}^3 \text{s}^{-1} \text{eV}^{-1}$

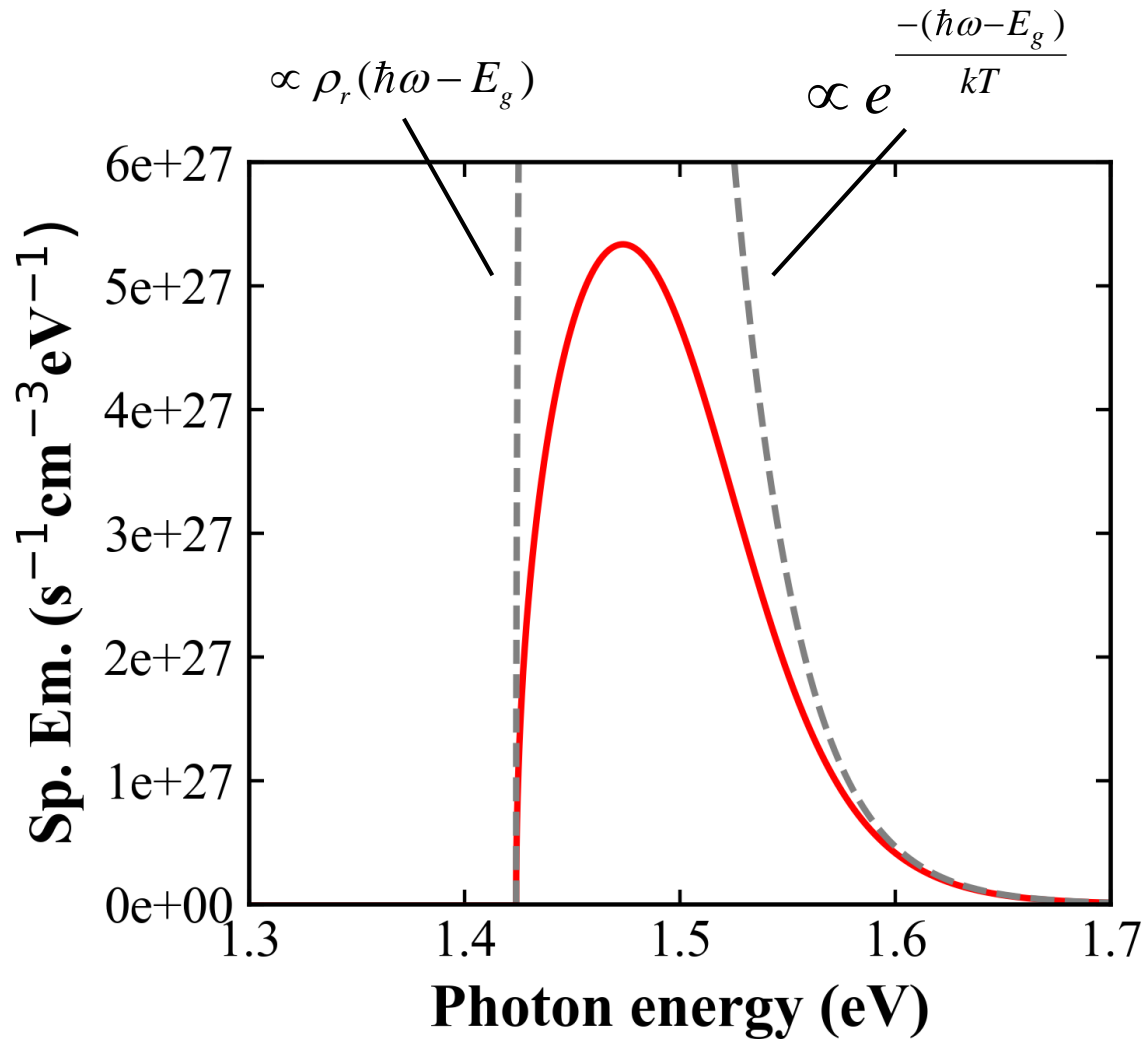
$$r_{\text{spont,bulk}}(\hbar\omega) = C_0 \left( \frac{n^2 \omega^2}{\pi^2 \hbar c^2} \right) |\hat{e} \cdot \mathbf{p}_{cv}|^2 \rho_{r,\text{bulk}}(\hbar\omega - E_g) f_c(\hbar\omega - E_g) (1 - f_v(\hbar\omega - E_g))$$

# Spontaneous emission spectrum





# Spontaneous emission spectrum



For  $\hbar\omega \approx E_g$

Limited by density of states

$$r_{\text{spont}} \propto \rho_r(\hbar\omega - E_g)$$

For  $\hbar\omega \gg F_c - F_v$

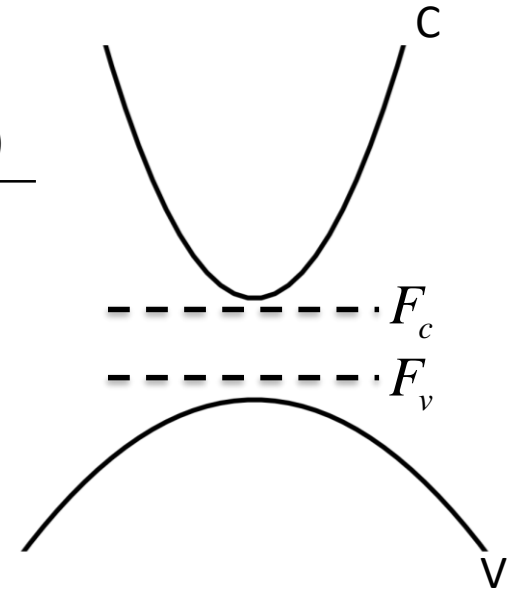
Limited by filling of states

$$r_{\text{spont}} \propto e^{-\frac{(\hbar\omega - E_g)}{kT}}$$

# Low-injection

For low-injection (Quasi-Fermi levels are within the bandgap)

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$$f_c \approx \exp\left(\frac{F_c - E_g - (\hbar\omega - E_g)(m_r^*/m_e^*)}{kT}\right)$$

$$(1 - f_v) \sim \exp\left(\frac{-(\hbar\omega - E_g)(m_r^*/m_h^*) - F_v}{kT}\right)$$

$$f_c(1 - f_v) \approx \exp\left(\frac{F_c - E_g - (\hbar\omega - E_g)(m_r^*/m_e^*) - (\hbar\omega - E_g)(m_r^*/m_h^*) - F_v}{kT}\right)$$

$$= \exp\left(\frac{-(\hbar\omega - E_g)}{kT}\right) \exp\left(\frac{-E_g}{kT}\right) \exp\left(\frac{F_c - F_v}{kT}\right)$$

$$= \exp\left(\frac{-(\hbar\omega - E_g)}{kT}\right) \frac{np}{N_c N_v}$$

$N_c, N_v$  (effective density of states)

# Radiative rate

$$r_{\text{spont,bulk}}(\hbar\omega) = C_0 \left( \frac{n^2 \omega^2}{\pi^2 \hbar c^2} \right) |\hat{e} \cdot \mathbf{p}_{cv}|^2 \rho_{r,\text{bulk}}(\hbar\omega - E_g) \exp\left(\frac{-(\hbar\omega - E_g)}{kT}\right) \frac{np}{N_c N_v}$$

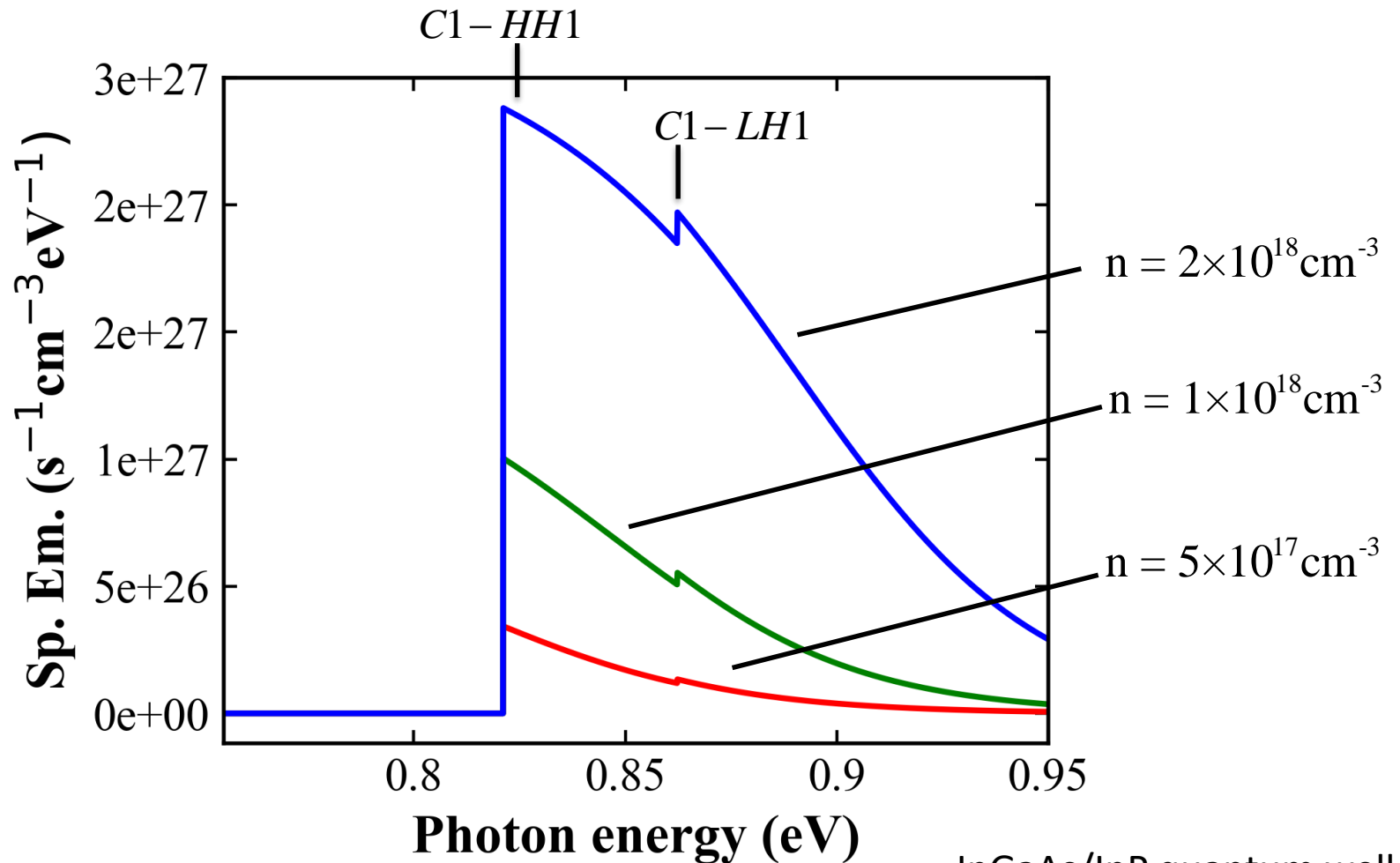
Radiative rate  
 $\text{cm}^{-3}\text{s}^{-1}$

$$R_{\text{rad}} = \int r_{\text{spont,bulk}}(\hbar\omega) d(\hbar\omega) = B_0 np$$

Material	$B_0$ ( $\text{cm}^3\text{s}^{-1}$ )
GaAs	$2.0 \times 10^{-10}$
InP	$1.2 \times 10^{-10}$
GaN	$2.2 \times 10^{-10}$
GaP	$3.9 \times 10^{-13}$
Si	$3.2 \times 10^{-14}$
Ge	$2.8 \times 10^{-13}$

# Quantum well

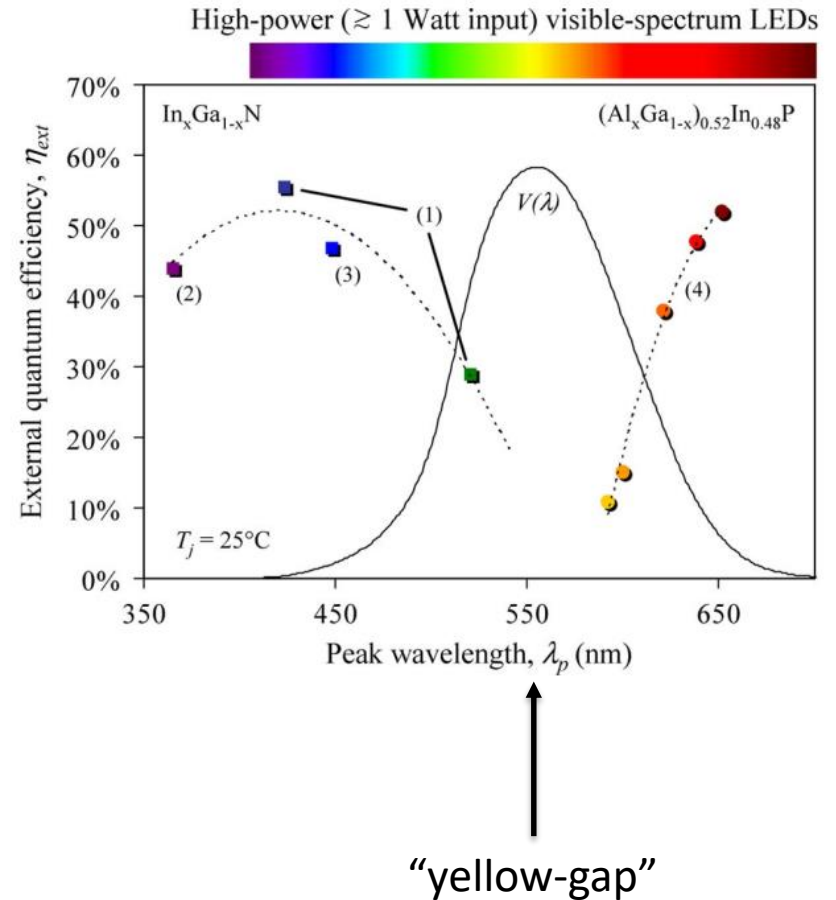
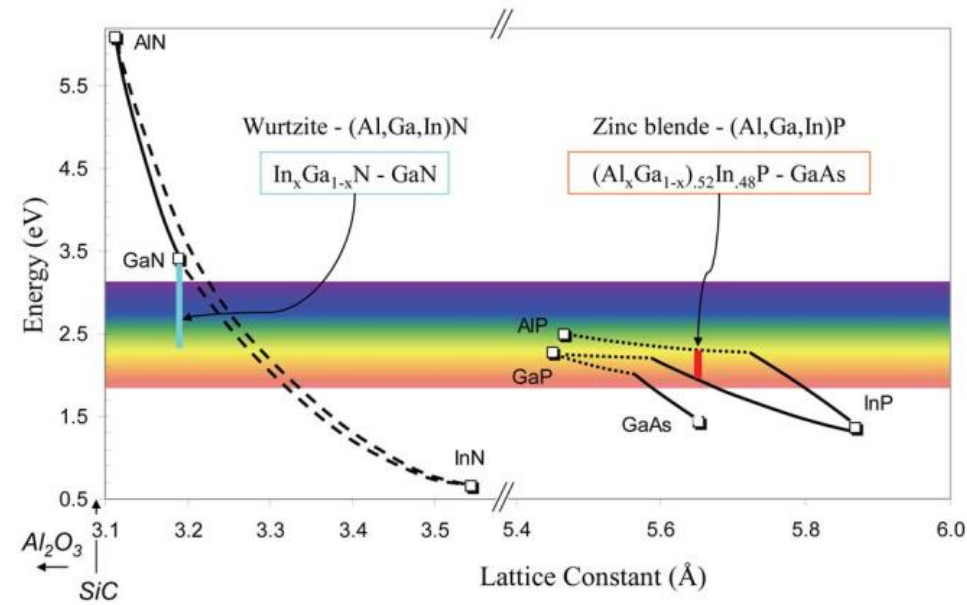
$$r_{\text{spont},\text{QW}} = C_0 \left( \frac{n^2 \omega^2}{\pi^2 \hbar c^2} \right) \frac{1}{L_z} \sum_{hh, lh} \sum_{n, m} |I_{hm}^{en}|^2 |\hat{e} \cdot \mathbf{p}_{cv}|^2 \rho_{r, \text{QW}} H(\hbar\omega - E_{hm}^{en}) f_c(\hbar\omega - E_{hm}^{en}) (1 - f_v(\hbar\omega - E_{hm}^{en}))$$



InGaAs/InP quantum well  
6nm thick, T=300K

Note: Linewidth effects are ignored

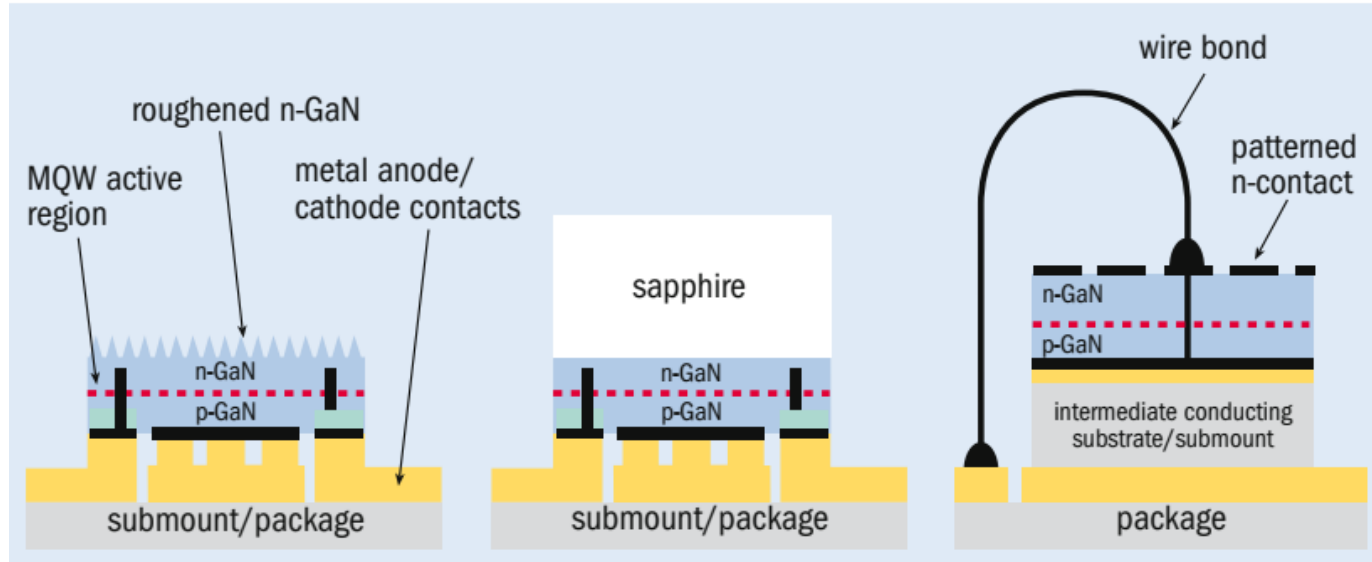
# Light emitting diodes



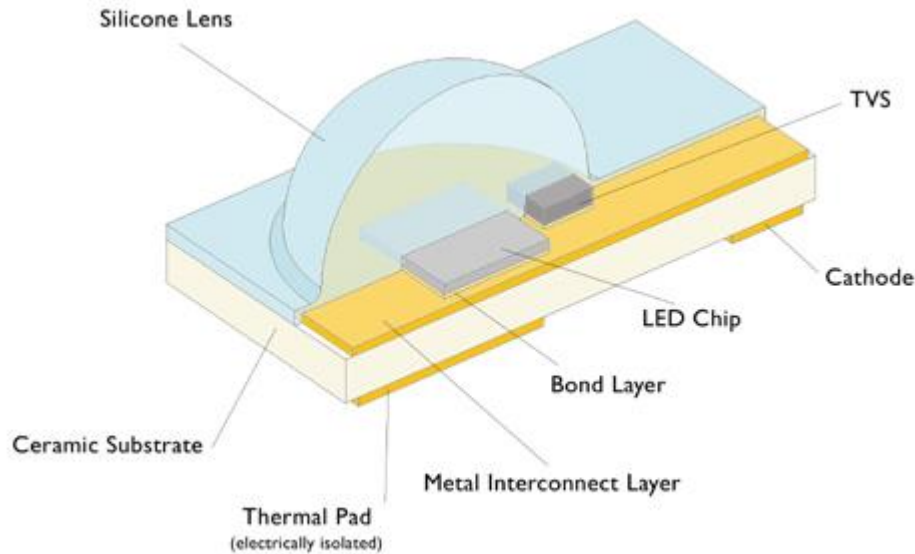
Thin-film flip chip

flip chip

vertically-injected thin film



Source: Compound Semiconductor



Source: Lumileds

